

General purpose (dual transistors)

IMX8

●Features

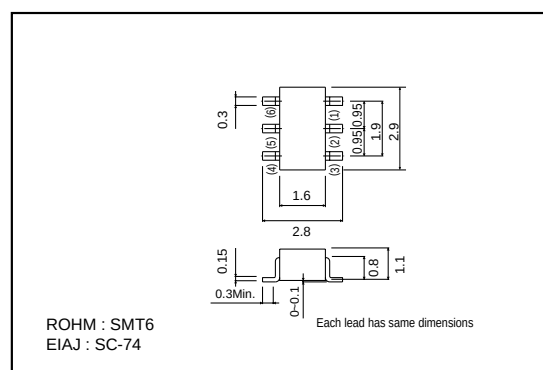
- 1) Two 2SC3906K chips in an SMT package.
- 2) High breakdown voltage.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	120	V
Collector-emitter voltage	V_{CE0}	120	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	50	mA
Power dissipation	P_C	300(TOTAL)	mW *
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* 200mW per element must not be exceeded.

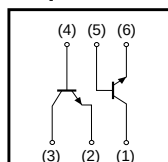
●External dimensions (Units : mm)



●Package, marking, and packaging specifications

Part No.	IMX8
Package	SMT6
Marking	X4
Code	T108
Basic ordering unit (pieces)	3000

●Equivalent circuit



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	120	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CE0}	120	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EB0}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=100V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
DC current transfer ratio	h_{FE}	180	—	820	—	$V_{CE}=6V, I_C=2mA$
Transition frequency	f_T	—	140	—	MHz	$V_{CE}=12V, I_E=2mA, f=100MHz$ *
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C/I_E=10mA/1mA$

*Transition frequency of the device